

Schottky barrier diode

RB521S-30

●Applications

Low current rectification and high speed switching

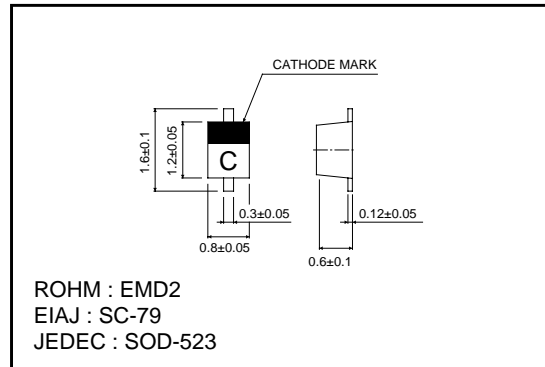
●Features

- 1) Extremely small surface mounting type. (EMD2)
- 2) $I_o=200\text{mA}$ guaranteed despite the size.
- 3) Low V_F . ($V_F=0.40\text{V}$ Typ. At 200mA)

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	$-40\text{--}+125$	$^\circ\text{C}$

* 60Hz for 1 ms

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.50	V	$I_F = 200\text{mA}$
Reverse current	I_R	–	–	30	μA	$V_R = 10\text{V}$

Note) sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

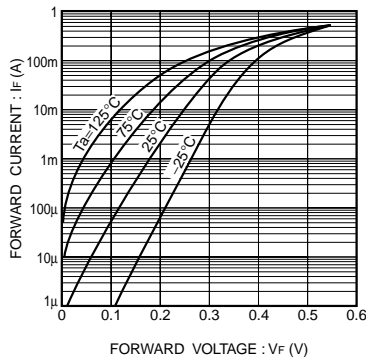


Fig. 1 Forward characteristics

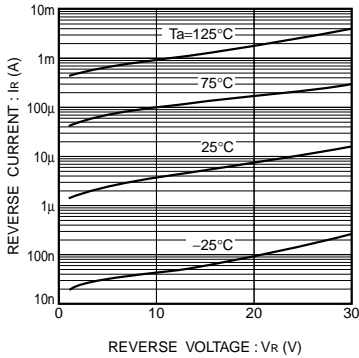


Fig. 2 Reverse characteristics

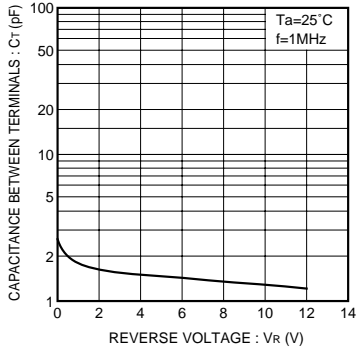


Fig. 3 Capacitance between terminals characteristics

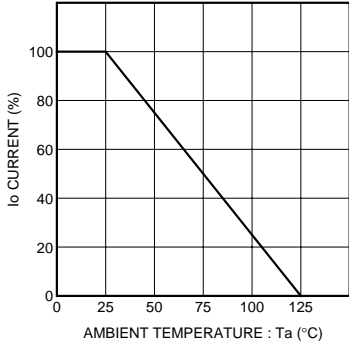


Fig. 4 Derating curve (mounting on glass epoxy PCBs)